

## **JTDB 25**

25 Watts, 36 Volts, Pulsed Avionics 960 - 1215 MHz

#### **GENERAL DESCRIPTION**

The JTDB 25 is a high power COMMON BASE bipolar transistor. It is designed for pulsed systems in the frequency band 960-1215 MHz. The device has gold thin-film metallization and diffused ballasting for proven highest MTTF. The transistor includes input and output prematch for broadband capability. Low thermal resistance package reduces junction temperature, extends life.

#### ABSOLUTE MAXIMUM RATINGS

Maximum Power Dissipation @ 25°C<sup>2</sup> 97 Watts

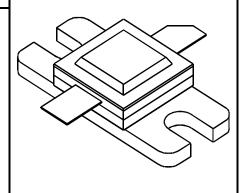
Maximum Voltage and Current

BVcesCollector to Base Voltage55 VoltsBVeboEmitter to Base Voltage3.5 VoltsIcCollector Current5.0 Amps

**Maximum Temperatures** 

Storage Temperature  $-65 \text{ to} + 200^{\circ}\text{C}$ Operating Junction Temperature  $+200^{\circ}\text{C}$ 

# CASE OUTLINE 55AW, STYLE 1



#### ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$\begin{array}{c} \textbf{Pout} \\ \textbf{Pin} \\ \textbf{Pg} \\ \eta_c \\ \textbf{VSWR} \end{array}$	Power Out Power Input Power Gain Collector Efficiency Load Mismatch Tolerance	$F = 960-1215 \text{ MHz}$ $Vcc = 36 \text{ Volts}$ $PW = 10  \mu\text{sec}$ $DF = 40\%$ $F = 1090 \text{ MHz}$	25 7.0	7.5 40	5.0 5:1	Watts Watts dB %

BVebo	Emitter to Base Breakdown	Ie = 5  mA	3.5		Volts
BVces	Collector to Emitter Breakdown	Ic = 10  mA	55		Volts
$\mathbf{h}_{\mathbf{FE}}$	DC - Current Gain	Ic = 500  mA, Vce = 5  V	10		
$\Theta \mathbf{j} \mathbf{c}^2$	Thermal Resistance			1.8	°C/W

Note 1: At rated output power and pulse conditions

2: At rated pulse conditions

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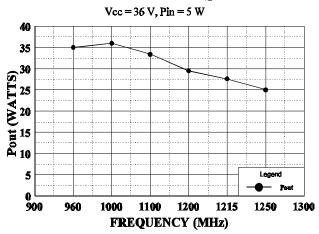
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#### All Data shown is for operation under the rated pulse conditions.

#### POWER OUTPUT vs FREQUENCY



## SERIES INPUT IMPEDANCE vs FREQUENCY Vcc = 36 V, Pin = 5 W

# 8 + 1X (OHMS)

1100

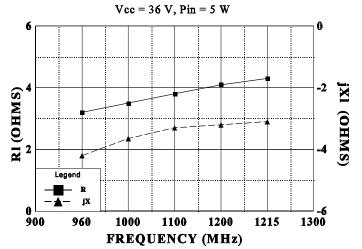
FREQUENCY (MHz)

1200

1215

1300

### SERIES LOAD IMPEDANCE vs FREQUENCY



July 1997

2

900

јх 960

1000

10

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